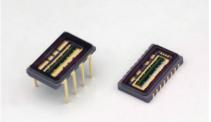
HAMAMATSU



CMOS linear image sensors

S9226 series

Built-in timing generator and signal processing circuit; 3.3 V single supply operation

The S9226 series is a small CMOS linear image sensor designed for image input applications. The signal processing circuit has a charge amplifier with excellent input/output characteristics. Two package styles are provided: a DIP type and a surface mount type.

Features

- Pixel pitch: 7.8 μm
 Pixel height: 125 μm
- **1024 pixels**
- 3.3 V single power supply operation available
- High sensitivity, low dark current, low noise
- On-chip charge amplifier with excellent input/output characteristics
- Built-in timing generator allows operation with only start and clock pulse inputs.
- ➡ Video data rate: 200 kHz max.
- → Spectral response range: 400 to 1000 nm
- **■** Two package styles are provided:

DIP (dual inline package) type: S9226-03

Surface mount type: S9226-04

Applications

- Analytical instruments
- Position detection
- **■** Image reading

Absolute maximum ratings

Parameter	Symbol	Value	Unit
Supply voltage	Vdd	-0.3 to +6	V
Gain selection terminal voltage	Vg	-0.3 to +6	V
Clock pulse voltage	V(CLK)	-0.3 to +6	V
Start pulse voltage	V(ST)	-0.3 to +6	V
Operating temperature*1	Topr	-5 to +60	°C
Storage temperature*1	Tstg	-10 to +70	°C

^{*1:} No condensation

Shape specifications

Parameter	Specification	Unit
Number of pixels	1024	-
Pixel pitch	7.8	μm
Pixel height	125	μm
Active area length	7.9872	mm
Package	Ceramic	-
Window material	Tempax	-

= Recommended terminal voltage (Ta=25 °C)

Parameter		Symbol	Min.	Тур.	Max.	Unit
Supply voltage		Vdd	3.3	5	5.25	V
Gain selection terminal voltage	High gain	Va	-	0	-	V
Gain Selection terminal voltage	Low gain	Vg	Vdd - 0.25	Vdd	Vdd + 0.25	V
	High level	V(CLK)	Vdd - 0.25	Vdd	Vdd + 0.25	V
	Low level	V(CLK)	-	0	-	V
Start pulse voltage	High level	V/(CT)	Vdd - 0.25	Vdd	Vdd + 0.25	V
	Low level	V(ST)	-	0	-	V

■ Electrical characteristics [Ta=25 °C, Vdd=5 V, V(CLK)=V(ST)=5 V]

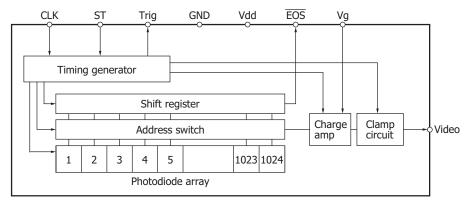
Parameter		Symbol	Min.	Тур.	Max.	Unit
Clock pulse frequency		f(CLK)	10 k	-	800 k	Hz
Video data rate		VR	-	f(CLK)/4	-	Hz
Power consumption		Р	20	30	40	mW
Conversion efficiency	High gain	CE	-	3.2	-	11///0-
Conversion emclency	Low gain	CE	-	1.6	-	μV/e-
Output impedance*2		Zo	-	185	-	Ω

■ Electrical and optical characteristics [Ta=25 °C, Vdd=5 V, V(CLK)=V(ST)=5 V]

Parameter		Symbol	Min.	Тур.	Max.	Unit	
Spectral response range		λ		400 to 1000			
Peak sensitivity wavelength		λр	-	- 650 -			
Dark current		ID	-	5	50	fA	
Dark output voltage*3	High gain	Vd	-	1	10	m)/	
Dark output voltage*3	Low gain	va	-	0.5	5	mV	
Saturation output voltage*4		Vsat	2.2	3.2	-	V	
Deadaut naise	High gain	Nr	-	1.4	2.2	ma\/ wma.c	
Readout noise	Low gain	INI	-	0.7	1.1	mV rms	
Offset output voltage		Vo	0.2	0.35	0.6	V	
Photo response non-uniformity*5 *6		PRNU		-	±5	%	

^{*2:} An increased current consumption at the video output terminal rises the sensor chip temperature causing an increased dark current. Connect a buffer amplifier for impedance conversion to the video output terminal so that the current flow is minimized. Use a JFET or CMOS input, high-impedance input op amp as the buffer amplifier.

Block diagram



KMPDC0165EC



^{*3:} Integration time=10 ms

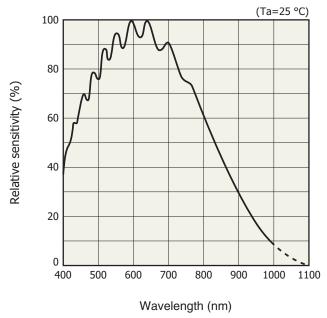
^{*4:} Voltage difference with respect to Vo

^{*5:} Uniformity is measured using 1022 pixels excluding the pixels at both ends under the condition that the device is uniformly illuminated by light which is 50% of the saturation level, and is defined as follows: PRNU = ΔX/X × 100 (%)

X: the average output of all pixels, ΔX : difference between X and maximum or minimum output

^{*6:} Measured with a tungsten lamp of 2856 K

Spectral response (typical example)



KMPDB0229EC

Resolution

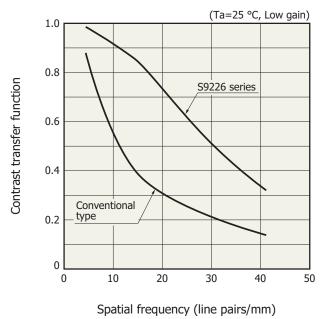
CTF: contrast transfer function

$$CTF = \frac{VWO - VBO}{VW - VB}$$

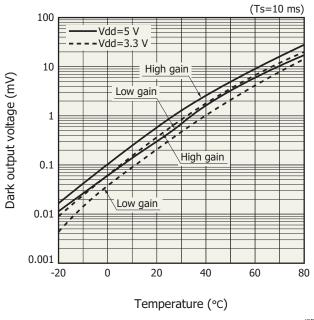
Vwo: output white level VBO: output black level

Vw : output white level (when input pattern pulse width is wide)
VB : output black level (when input pattern pulse width is wide)

- Contrast transfer function vs. spatial frequency (typical example)

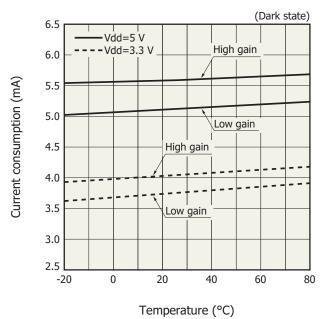


→ Dark output voltage vs. temperature (typical example)



KMPDB0319EA

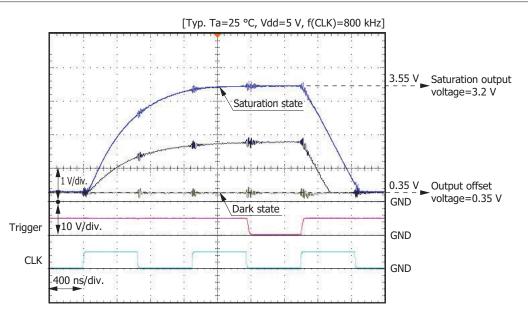
Current consumption vs. temerature (typical example)



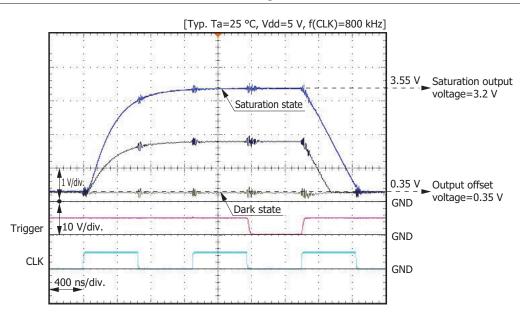
KMPDB0320EA

- Output waveform of one element

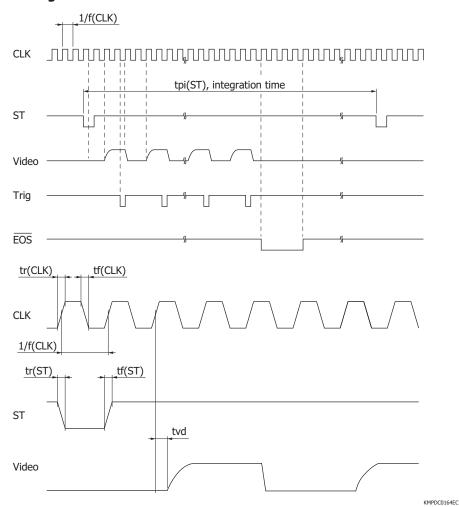




Low gain



- Timing chart



Parameter	Symbol	Min.	Тур.	Max.	Unit
Start pulse interval	tpi(ST)	4104/f(CLK)	-	-	S
Start pulse rise and fall times	tr(ST), tf(ST)	0	20	30	ns
Clock pulse duty	-	40	50	60	%
Clock pulse rise and fall times	tr(CLK), tf(CLK)	0	20	30	ns
Video delay time*7	tvd	10	20	30	ns

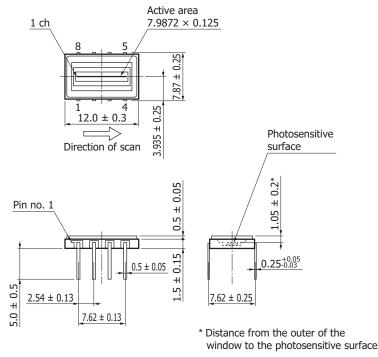
^{*7:} Ta=25 °C, Vdd=5 V, V(CLK)=V(ST)=5 V

Note: The CLK pulse should be set from high to low just once when the st pulse is low. The internal shift register starts operating at this timing.

The integration time is determined by the start pulse interval. However, since the charge integration of each pixel is carried out between the signal readout of that pixel and the next signal readout of the same pixel, the start time of charge integration differs depending on each pixel. In addition, the next start pulse cannot be input until signal readout from all pixels is completed.

- Dimensional outlines (unit: mm)

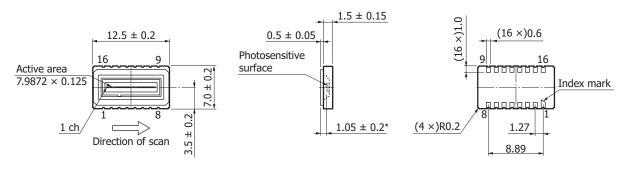
S9226-03



Pin no.	Symbol	Pin name	Input/Output
1	GND	Ground	Input
2	CLK	Clock pulse	Input
3	Trig	Trigger pulse	Output
4	ST	Start pulse	Input
5	Vg	Gain selection voltage	Input
6	Video	Video output	Output
7	EOS	End of scan	Output
8	Vdd	Supply voltage	Input

KMPDA0172ED

S9226-04



* Distance from the outer of the window to the photosensitive surface

KMPDA0258FA

Pin no.	Symbol	Pin name	Input/Output	Pin no.	Symbol	Pin name	Input/Output
1	NC	No connection		9	NC	No connection	
2	NC	No connection		10	NC	No connection	
3	GND	Ground	Input	11	Vg	Gain selection voltage	Input
4	CLK	Clock pulse	Input	12	Video	Video output	Output
5	Trig	Trigger pulse	Output	13	EOS	End of scan	Output
6	ST	Start pulse	Input	14	Vdd	Supply voltage	Input
7	NC	No connection		15	NC	No connection	
8	NC	No connection		16	NC	No connection	

Precautions during use

(1) Electrostatic countermeasures

This device has a built-in protection circuit against static electrical charges. However, to prevent destroying the device with electrostatic charges, take countermeasures such as grounding yourself, the workbench and tools to prevent static discharges. Also protect this device from surge voltages which might be caused by peripheral equipment.

(2) Light input window

If the incident window is contaminated or scratched, the output uniformity will deteriorate considerably, so care should be taken in handling the window. Avoid touching it with bare hands.

The window surface should be cleaned before using the device. If dry cloth or dry cotton swab is used to rub the window surface, static electricity may be generated, and therefore this practice should be avoided. Use soft cloth, cotton swab or soft paper moistened with ethyl alcohol to wipe off dirt and foreign matter on the window surface.

(3) Soldering

To prevent damaging the device during soldering, take precautions to prevent excessive soldering temperatures and times. Soldering should be performed within 5 seconds at a soldering temperature below 260 °C.

(4) Reflow soldering

Soldering conditions may differ depending on the board size, reflow furnace, etc. Check the conditions before soldering. A sudden temperature rise and cooling may be the cause of trouble, so make sure that the temperature change is within 4 °C per second.

The bonding portion between the ceramic base and the glass may discolor after reflow soldering, but this has no adverse effects on the hermetic sealing of the product.

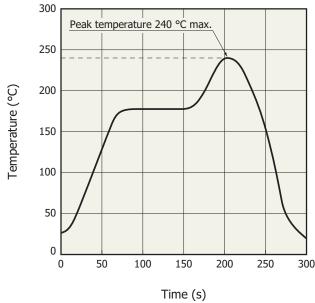
(5) Operating and storage environments

Always observe the rated temperature range when handling the device. Operating or storing the device at an excessively high temperature and humidity may cause variations in performance characteristics and must be avoided.

(6) UV exposure

This product is not designed to prevent deterioration of characteristics caused by UV exposure, so do not expose it to UV light.

Recommended solder reflow condition



KAPDB0169EA

S9226 series

Information described in this material is current as of December, 2010. Product specifications are subject to change without prior notice due to improvements or other reasons. Before assembly into final products, please contact us for the delivery specification sheet to check the latest information.

Type numbers of products listed in the delivery specification sheets or supplied as samples may have a suffix "(X)" which means preliminary specifications or a suffix "(Z)" which means developmental specifications.

The product warranty is valid for one year after delivery and is limited to product repair or replacement for defects discovered and reported to us within that one year period. However, even if within the warranty period we accept absolutely no liability for any loss caused by natural disasters or improper product use. Copying or reprinting the contents described in this material in whole or in part is prohibited without our prior permission.

HAMAMATSU

www.hamamatsu.com

HAMAMATSU PHOTONICS K.K., Solid State Division

1126-1 Ichino-cho, Higashi-ku, Hamamatsu City, 435-8558 Japan, Telephone: (81) 53-434-3311, Fax: (81) 53-434-5184
U.S.A.: Hamamatsu Corporation: 360 Foothill Road, P.O.Box 6910, Bridgewater, N.J. 08807-0910, U.S.A., Telephone: (1) 908-231-0966, Fax: (1) 908-231-1218
Germany: Hamamatsu Photonics Deutschland GmbH: Arzbergestr. 10, D-82211 Herrsching am Ammersee, Germany; Telephone: (49) 8152-375-0, Fax: (49) 8152-265-8
France: Hamamatsu Photonics France S.A.R.L.: 19, Rue du Saule Trapu, Parc du Moulin de Massy, 91882 Massy Cedex, France, Telephone: 33-(1) 69 53 71 00, Fax: 33-(1) 69 53 71 10
United Kingdom: Hamamatsu Photonics UK Limited: 2 Howard Court, 10 Tewin Road, Welwyn Garden City, Hertfordshire AL7 1BW, United Kingdom, Telephone: (44) 1707-294888, Fax: (44) 1707-32577
North Europe: Hamamatsu Photonics Norden AB: Smidesvägen 12, SE-171 41 Solna, Sweden, Telephone: (46) 8-509-031-00, Fax: (46) 8-509-031-01
Italy: Hamamatsu Photonics Italia S.R.L.: Strada della Moia, 1 int. 6, 20020 Arese, (Milano), Italy, Telephone: (39) 02-935-81-733, Fax: (39) 02-935-81-741